MH1M08A0AJ-6,-7,-8/ MH1M08A0AJA-6,-7,-8

FAST PAGE MODE 8388608-BIT(1048576-WORD BY 8-BIT)DYNAMIC RAM

DESCRIPTION

The MH1M08A0AJ/JA is 1048576-word × 8-bit dynamic RAM and consists of two industry standard 1M × 4 dynamic RAMs in SOJ.

The mounting of SOJ on a single in-line package provides any application where high densities and large quantities of memory are required.

FEATURES

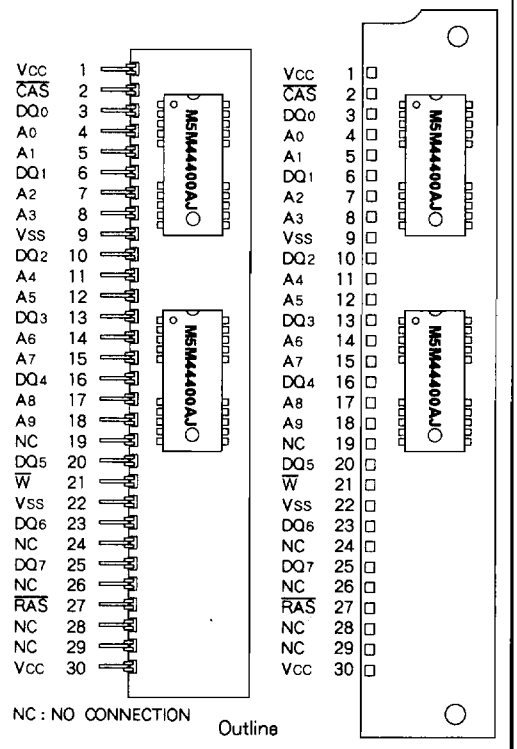
Type name	Access time (max) (ns)	Cycle time (min) (ns)	Power dissipation (typ) (mW)
MH1M08A0AJ-6 MH1M08A0AJA-6	60	120	800
MH1M08A0AJ-7 MH1M08A0AJA-7	70	140	700
MH1M08A0AJ-8 MH1M08A0AJA-8	80	160	600

- Utilizes industry standard 4M RAMs in SOJ and 1M RAM in SOJ
- 30 pins Single in-line Package
- Sinngle + 5V (± 10%) supply operation
- Low stand by power dissipation ····· 11mW (max)
- Low operation power dissipation
  - MH1M08A0AJ-6/MH1M08A0AJA-6 ····· 1.10W (max)
  - MH1M08A0AJ-7/MH1M08A0AJA-7 ····· 0.94W (max)
  - MH1M08A0AJ-8/MH1M08A0AJA-8 ····· 0.83W (max)
- All inputs, output TTL compatible and low capacitance
- Includes (0.22 μF × 2) decoupling capacitors
- 1024 refresh cycles every 16.4ms (A_0~A_9)

APPLICATION

Main-memory unit for computers, Microcomputer memory, Refresh memory for CRT

PIN CONFIGURATION(TOP VIEW) (Single side)

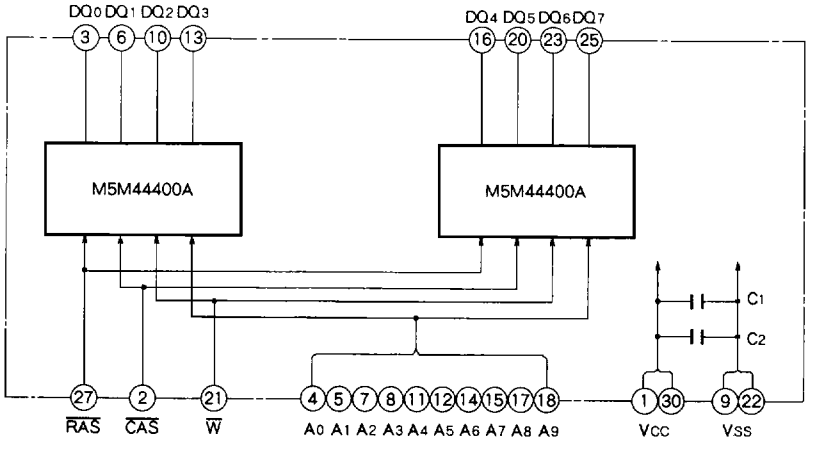


NC : NO CONNECTION

Outline

30N5F (MH1M08A0AJA) 30N9G (MH1M08A0AJ)

BLOCK DIAGRAM



FUNCTION

The MH1M08A0AJ/JA provide, in addition to normal read, write a number of other functions, e・g・, fast page mode, $\overline{RAS}$ only refresh. The input conditions for each are shown in Table 1.

Table 1 Input conditions for each mode

Operation	Inputs					Input/Output		Refresh	Remark
	$\overline{RAS}$	$\overline{CAS}$	$\overline{W}$	Row address	Column address	Input	Output		
Read	ACT	ACT	NAC	APD	APD	OPN	VLD	YES	Fast page mode identical
Write (Early write)	ACT	ACT	ACT	APD	APD	VLD	OPN	YES	
$\overline{RAS}$-only refresh	ACT	NAC	DNC	APD	DNC	DNC	OPN	YES	
Hidden refresh	ACT	ACT	DNC	APD	DNC	OPN	VLD	YES	
$\overline{CAS}$ before $\overline{RAS}$ refresh	ACT	ACT	DNC	DNC	DNC	DNC	OPN	YES	
Stand by	NAC	DNC	DNC	DNC	DNC	DNC	OPN	NO	

Note : ACT : active. NAC : nonactive. DNC : don't care. VLD : valid. IVD : Invalid. APD : applied. OPN : open

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Unit
V_{CC}	Supply voltage	With respect to Vss	−1~7	V
V_I	Input voltage		−1~7	V
V_O	Output voltage		−1~7	V
I_O	Output current		50	mA
P_d	Power dissipation	Ta = 25℃	2	W
T_{opr}	Operating temperature		0~70	℃
T_{stg}	Storage temperature		−40~125	℃

RECOMMENDED OPERATING CONDITIONS (Ta = 0~70℃, unless otherwise noted) (Note 1)

Symbol	Parameter	Limits			Unit
		Min	Nom	Max	
V_{CC}	Supply voltage	4.5	5	5.5	V
V_{SS}	Supply voltage	0	0	0	V
V_{IH}	High-level input voltage, all inputs	2.4		6.5	V
V_{IL}	Low-level input voltage, all inputs	−2.0		0.8	V

Note 1 : All voltage values are with respect to Vss.

ELECTRICAL CHARACTERISTICS (T_a = 0~70℃, V_{CC} = 5V ± 10%, V_{SS} = 0V, unless otherwise noted) (Note 2)

Symbol	Parameter		Test conditions	Limits			Unit
				Min	Typ	Max	
V_{OH}	High-level output voltage		I_{OH} = −5mA	2.4		V_{CC}	V
V_{OL}	Low-level output voltage		I_{OL} = 4.2mA	0		0.4	V
I_{OZ}	Off-state output current		Q floating 0V ≦ V_{OUT} ≦ 5.5V	−10		10	μA
I_I	Input current		0V≦V_{IN}≦6.5V, Other inputs pins=0V	−10		10	μA
$I_{CC1(AV)}$	Average supply current from V_{CC}, operating (Note 3, 4)	MH1M08A0A-6	$\overline{RAS}$, $\overline{CAS}$ cycling t_{CR} = t_{WC} = min. output open			200	mA
		MH1M08A0A-7				170	
		MH1M08A0A-8				150	
$I_{CC2(AV)}$	Supply current from V_{CC}, stand-by		$\overline{RAS}$ = $\overline{CAS}$ = V_{IH}, output open			4	mA
			$\overline{RAS}$ = $\overline{CAS}$ ≧ V_{CC} − 0.5			2	
$I_{CC3(AV)}$	Average supply current from V_{CC}, refreshing (Note 3)	MH1M08A0A-6	$\overline{RAS}$ cycling, $\overline{CAS}$ = V_{IH} t_{RC} = min. output open			200	mA
		MH1M08A0A-7				170	
		MH1M08A0A-8				150	
$I_{CC4(AV)}$	Average supply current from V_{CC} Fast-Page-Mode (Note 3, 4)	MH1M08A0A-6	$\overline{RAS}$ = V_{IL}, $\overline{CAS}$ cycling t_{PC} = min. output open			200	mA
		MH1M08A0A-7				170	
		MH1M08A0A-8				150	
$I_{CC6(AV)}$	Average supply current from V_{CC}, $\overline{CAS}$ before $\overline{RAS}$ refresh mode (Note 3)	MH1M08A0A-6	$\overline{CAS}$ before $\overline{RAS}$ refresh cycling t_{RC} = min. output open			170	mA
		MH1M08A0A-7				150	
		MH1M08A0A-8				130	

Note 2 : Current flowing into an IC is positive, out is negative.
3 : $I_{CC1(AV)}$, $I_{CC3(AV)}$ and $I_{CC4(AV)}$ are dependent on cycle rate. Maximum current is measured at the fastest cycle rate.
4 : $I_{CC1(AV)}$ and $I_{CC4(AV)}$ are dependent on output loading. Specified values are obtained with the output open.

CAPACITANCE (T_a = 0~70℃, V_{CC} = 5V ± 10%, V_{SS} = 0V, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$C_{I(A)}$	Input capacitance, address inputs	V_I = V_{SS} f = 1MHz V_i = 25mVrms			25	pF
$C_{I(W)}$	Input capacitance, write control input				20	pF
$C_{I(RAS)}$	Input capacitance, $\overline{RAS}$ input				20	pF
$C_{I(CAS)}$	Input capacitance, $\overline{CAS}$ input				20	pF
$C_{I/O}$	Input/Output capacitance, data ports				15	pF

SWITCHING CHARACTERISTICS (T_a = 0~70℃, V_{CC} = 5V ± 10%, V_{SS} = 0V, unless otherwise noted, See notes 5, 12, 13)

Symbol	Parameter	Limits						Unit
		MH1M08A0A-6		MH1M08A0A-7		MH1M08A0A-8		
		Min	Max	Min	Max	Min	Max	
t_{CAC}	Access time from $\overline{CAS}$ (Note 6, 7)		15		20		20	ns
t_{RAC}	Access time from $\overline{RAS}$ (Note 6, 8)		60		70		80	ns
t_{AA}	Column Address access time (Note 6, 9)		30		35		40	ns
t_{CPA}	Access time from $\overline{CAS}$ precharge (Note 6, 10)		35		40		45	ns
t_{CLZ}	Output low impedance time from $\overline{CAS}$ low (Note 6)	5		5		5		ns
t_{OFF}	Output disable time after $\overline{CAS}$ high (Note 11)	0	15	0	20	0	20	ns

Note 5 : An initial pause of 500 μs is required after power-up followed by a minimum of eight initialization cycles (any combination of cycles containing a $\overline{RAS}$ clock such as $\overline{RAS}$-Only refresh).
Note the $\overline{RAS}$ may be cycled during the initial pause. And any 8 $\overline{RAS}$ or $\overline{RAS}/\overline{CAS}$ cycles are required after prolonged periods (greater than 16.4ms) of $\overline{RAS}$ inactivity before proper device operation is achieved.
6 : Measured with a load circuit equivalent to 2TTL loads and 100pF.
7 : Assumes that $t_{RCD} \geqq t_{RCD}(max)$ and $t_{ASC} \geqq t_{ASC}(max)$.
8 : Assumes that $t_{RCD} \leqq t_{RCD}(max)$ and $t_{RAD} \leqq t_{RAD}(max)$. If t_{RCD} or t_{RAD} is greater than the maximum recommended value shown in this table, t_{RAC} will increase by amount that t_{RCD} or t_{RAD} exceeds the value shown.
9 : Assumes that $t_{RAD} \geqq t_{RAD}(max)$ and $t_{ASC} \leqq t_{ASC}(max)$.
10 : Assumes that $t_{CP} \leqq t_{CP}(max)$ and $t_{ASC} \geqq t_{ASC}(max)$.
11 : $t_{OFF}(max)$ defines the time at which the output achieves the high impedance state ($I_{OUT} \leqq | \pm 10\ \mu A |$) and is not reference to $V_{OH}(min)$ or $V_{OL}(max)$.

TIMING REQUIREMENTS (For Read, Write, Refresh, and Fast Page Cycles)
(T_a = 0~70℃, V_{CC} = 5V ± 10%, V_{SS} = 0V, unless otherwise noted, See notes 12, 13)

Symbol	Parameter	Limits						Unit
		MH1M08A0A-6		MH1M08A0A-7		MH1M08A0A-8		
		Min	Max	Min	Max	Min	Max	
t_{REF}	Refresh cycle time		16.4		16.4		16.4	ms
t_{RP}	$\overline{RAS}$ high pulse width	50		60		70		ns
t_{RCD}	Delay time, $\overline{RAS}$ low to $\overline{CAS}$ low (Note 14)	20	45	20	50	20	60	ns
t_{CRP}	Delay time, $\overline{CAS}$ high to $\overline{RAS}$ low	10		10		10		ns
t_{RPC}	Delay time, $\overline{RAS}$ high to $\overline{CAS}$ low	0		0		0		ns
t_{CPN}	$\overline{CAS}$ high pulse width	10		10		10		ns
t_{RAD}	Column address delay time from $\overline{RAS}$ low (Note 15)	15	30	15	35	20	40	ns
t_{ASR}	Row address setup time before $\overline{RAS}$ low	0		0		0		ns
t_{ASC}	Column address setup time before $\overline{CAS}$ low (Note 16)	0	10	0	10	0	15	ns
t_{RAH}	Row address hold time after $\overline{RAS}$ low	10		10		15		ns
t_{CAH}	Column address hold time after $\overline{CAS}$ low	15		15		20		ns
t_T	Transition time (Note 17)	3	50	3	50	3	50	ns

Note 12 : The timing requirements are assumed t_T = 5ns.
13 : $V_{IH}(min)$ and $V_{IL}(max)$ are reference levels for measuring timing of input signals.
14 : $t_{RCD}(max)$ is specified as a reference point only. If t_{RCD} is less than $t_{RCD}(max)$, access time is t_{RAC}. If t_{RCD} is greater than $t_{RCD}(max)$, access time is controlled exclusively by t_{CAC} or t_{AA}. $t_{RCD}(min)$ is specified as $t_{RCD}(min) = t_{RAH}(min) + 2t_T + t_{ASC}(min)$.
15 : $t_{RAD}(max)$ is specified as a reference point only. If $t_{RAD} \geqq t_{RAD}(max)$ and $t_{ASC} \leqq t_{ASC}(max)$, access time is controlled exclusively by t_{AA}.
16 : $t_{ASC}(max)$ is specified as a reference point only. If $t_{RCD} \geqq t_{RCD}(max)$ and $t_{ASC} \geqq t_{ASC}(max)$, access time is controlled exclusively by t_{CAC}.
17 : t_T is measured between $V_{IH}(min)$ and $V_{IL}(max)$.

Read and Refresh Cycles

Symbol	Parameter	Limits						Unit
		MH1M08A0A-6		MH1M08A0A-7		MH1M08A0A-8		
		Min	Max	Min	Max	Min	Max	
t_{RC}	Read cycle time	120		140		160		ns
t_{RAS}	$\overline{RAS}$ low pulse width	60	10000	70	10000	80	10000	ns
t_{CAS}	$\overline{CAS}$ low pulse width	15	10000	20	10000	20	10000	ns
t_{CSH}	$\overline{CAS}$ hold time after $\overline{RAS}$ low	60		70		80		ns
t_{RSH}	$\overline{RAS}$ hold time after $\overline{CAS}$ low	15		20		20		ns
t_{RCS}	Read Setup time before $\overline{CAS}$ low	0		0		0		ns
t_{RCH}	Read hold time after $\overline{CAS}$ high (Note 18)	0		0		0		ns
t_{RRH}	Read hold time after $\overline{RAS}$ high (Note 18)	10		10		10		ns
t_{RAL}	Column address to $\overline{RAS}$ hold time	30		35		40		ns

Note 18 : Either t_{RCH} or t_{RRH} must be satisfied for a read cycle.

Write Cycle(Early Write)

Symbol	Parameter	Limits						Unit
		MH1M08A0A-6		MH1M08A0A-7		MH1M08A0A-8		
		Min	Max	Min	Max	Min	Max	
t_{WC}	Write cycle time	120		140		160		ns
t_{RAS}	$\overline{RAS}$ low pulse width	60	10000	70	10000	80	10000	ns
t_{CAS}	$\overline{CAS}$ low pulse width	15	10000	20	10000	20	10000	ns
t_{CSH}	$\overline{CAS}$ hold time after $\overline{RAS}$ low	60		70		80		ns
t_{RSH}	$\overline{RAS}$ hold time after $\overline{CAS}$ low	15		20		20		ns
t_{WCS}	Write setup time before $\overline{CAS}$ low	0		0		0		ns
t_{WCH}	Write hold time after $\overline{CAS}$ low	10		15		15		ns
t_{CWL}	$\overline{CAS}$ hold time after $\overline{W}$ low	15		20		20		ns
t_{RWL}	$\overline{RAS}$ hold time after $\overline{W}$ low	15		20		20		ns
t_{WP}	Write pulse width	10		15		15		ns
t_{DS}	Data setup time before $\overline{CAS}$ low or $\overline{W}$ low	0		0		0		ns
t_{DH}	Data hold time after $\overline{CAS}$ low or $\overline{W}$ low	10		15		15		ns

Fast-Page Mode Cycle(Read, Early Write, Read-Write Cycle) (Note 19)

Symbol	Parameter	Limits						Unit
		MH1M08A0A-6		MH1M08A0A-7		MH1M08A0A-8		
		Min	Max	Min	Max	Min	Max	
t_{PC}	Fast page mode read/write cycle time	40		45		50		ns
t_{RAS}	$\overline{RAS}$ low pulse width for read write cycle (Note 20)	100	100000	115	100000	135	100000	ns
t_{CP}	$\overline{CAS}$ high pulse width (Note 21)	10	15	10	15	10	20	ns
t_{CPRH}	$\overline{RAS}$ hold time after $\overline{CAS}$ precharge	35		40		45		ns

Note 19 : All previously specified timing requirements and switching characteristics are applicable to their respective fast page mode cycle.
20 : t_{RAS}(min) is specified as two cycles of $\overline{CAS}$ input are performed.
21 : t_{CP}(max) is specified as a reference point only.

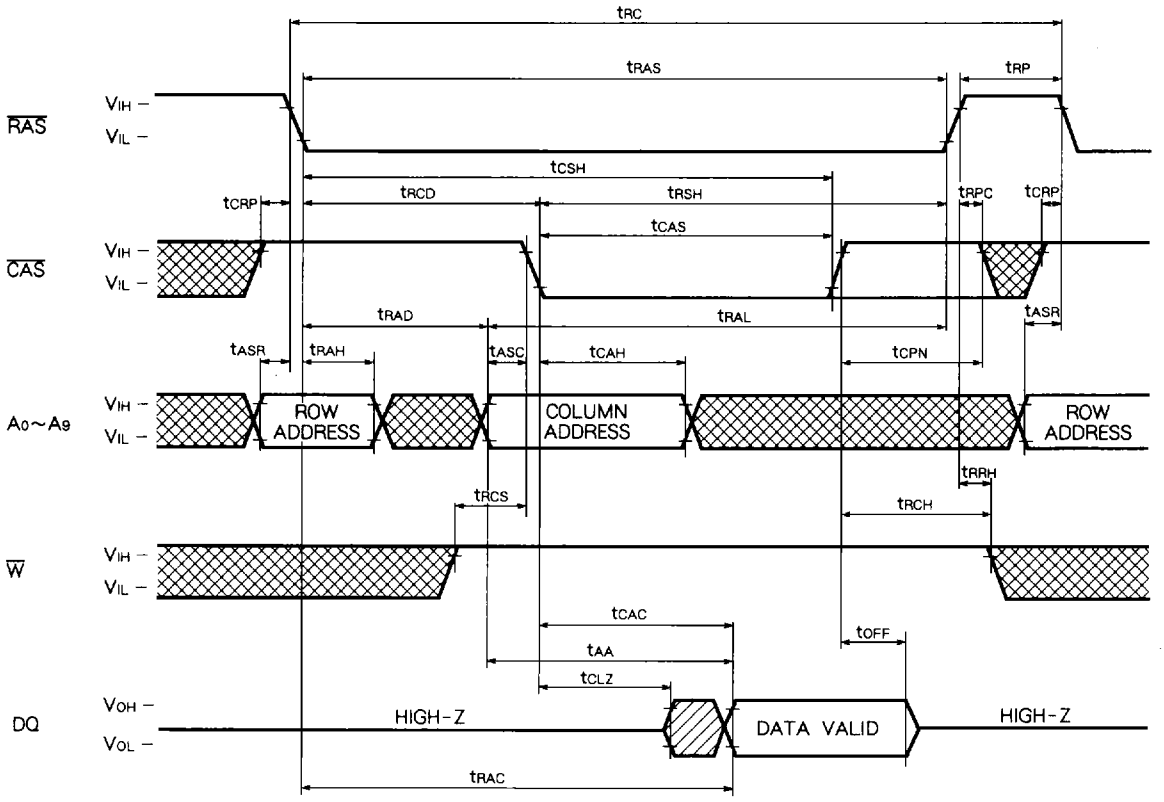
$\overline{CAS}$ before $\overline{RAS}$ Refresh Cycle (Note 22)

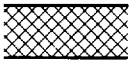
Symbol	Parameter	Limits						Unit
		MH1M08A0A-6		MH1M08A0A-7		MH1M08A0A-8		
		Min	Max	Min	Max	Min	Max	
t_{CSR}	$\overline{CAS}$ setup time before $\overline{RAS}$ low	10		10		10		ns
t_{CHR}	$\overline{CAS}$ hold time after $\overline{RAS}$ low	10		15		15		ns
t_{RSR}	Read setup time before $\overline{RAS}$ low	10		10		10		ns
t_{RHR}	Read hold time after $\overline{RAS}$ low	10		15		15		ns

Note 22 : Eight or more $\overline{CAS}$ before $\overline{RAS}$ cycles instead of eight $\overline{RAS}$ cycles are necessary for proper operation of $\overline{CAS}$ before $\overline{RAS}$ refresh mode.

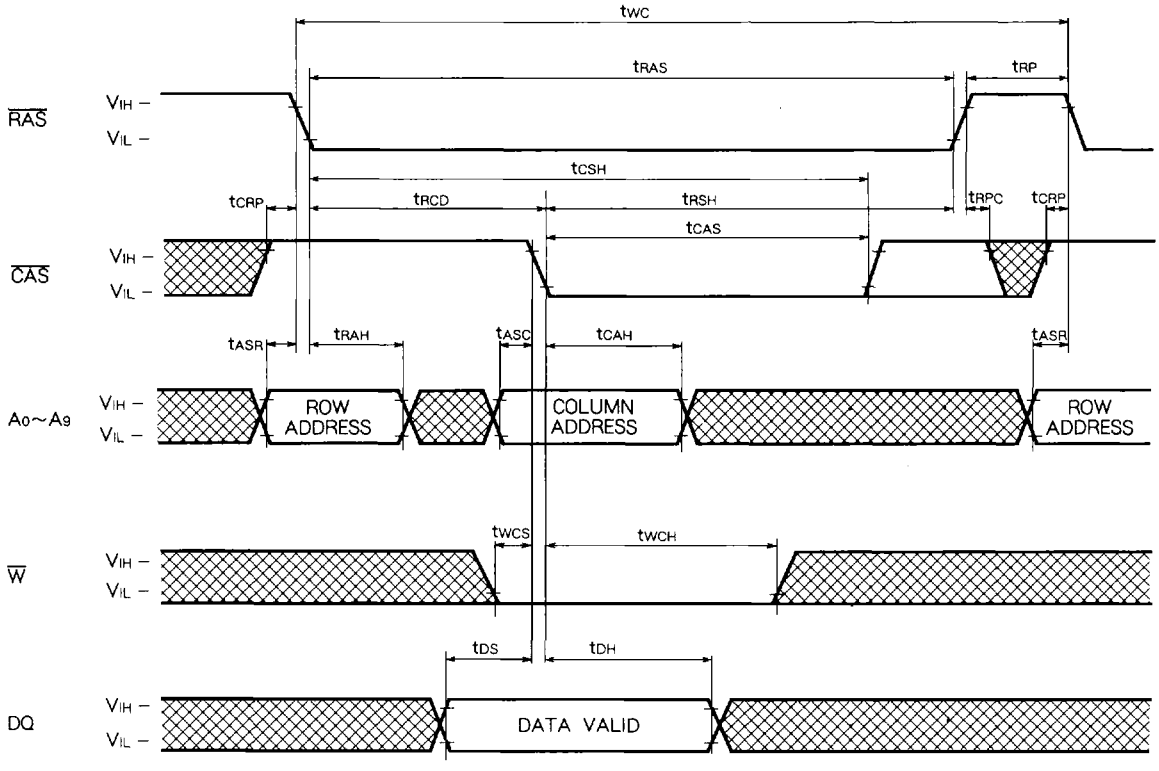
Timing Diagrams (Note 23)

Read Cycle

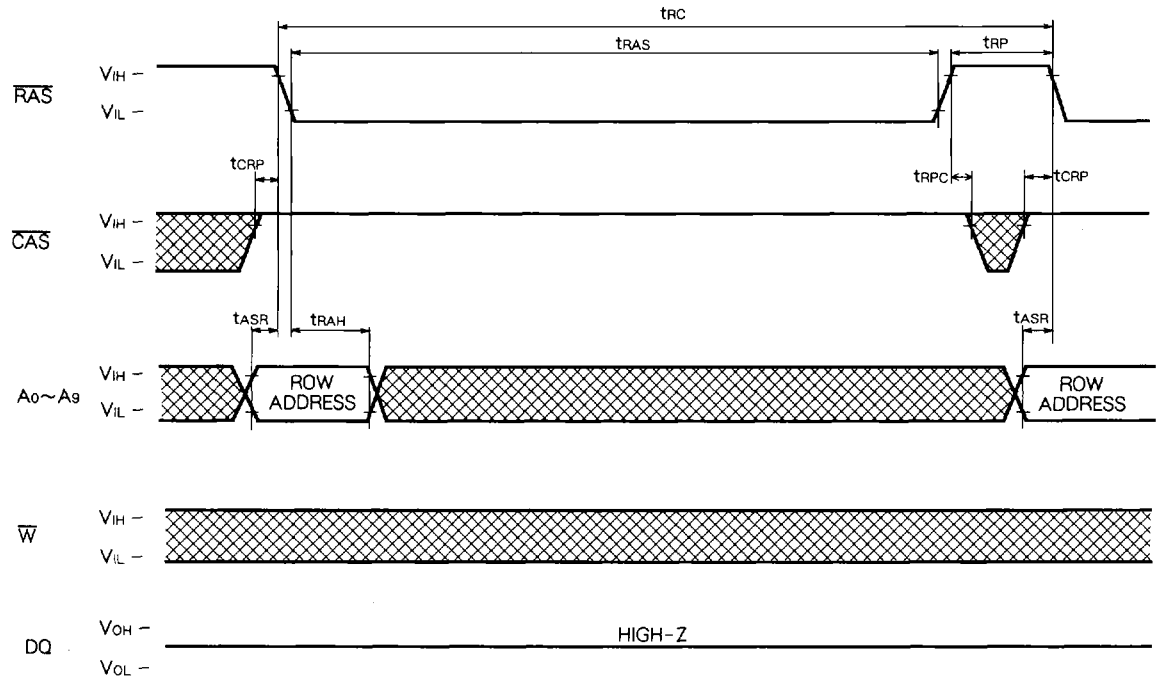


Note 23  Indicates the don't care input.

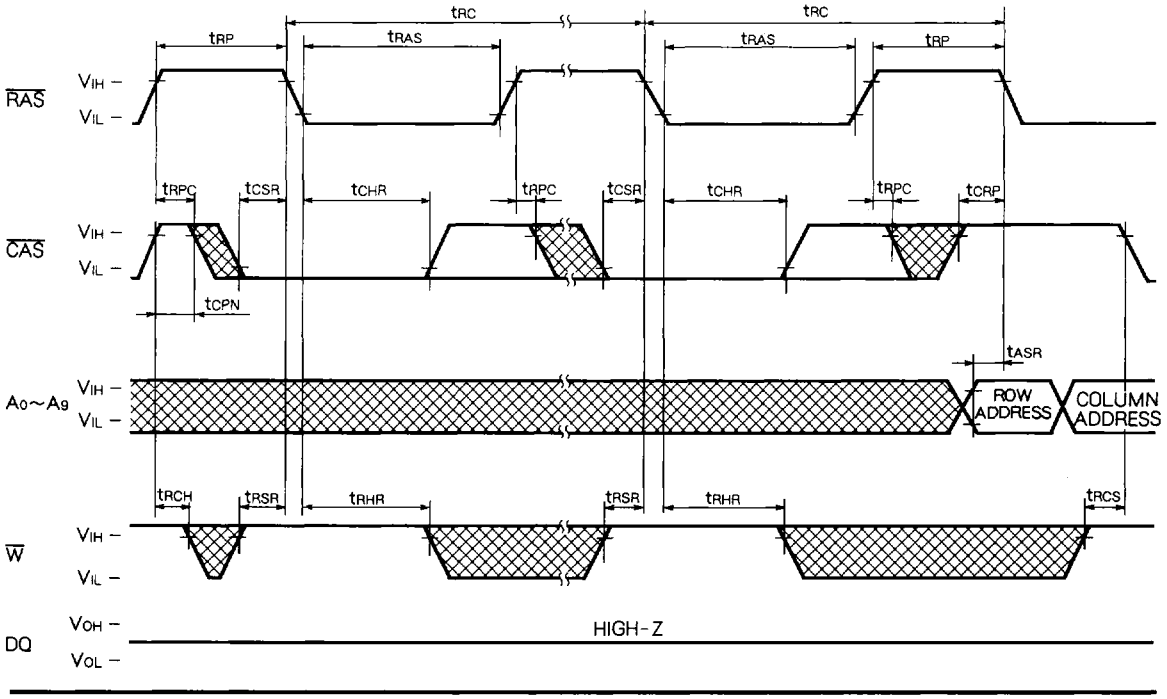
Write Cycle(Early Write)



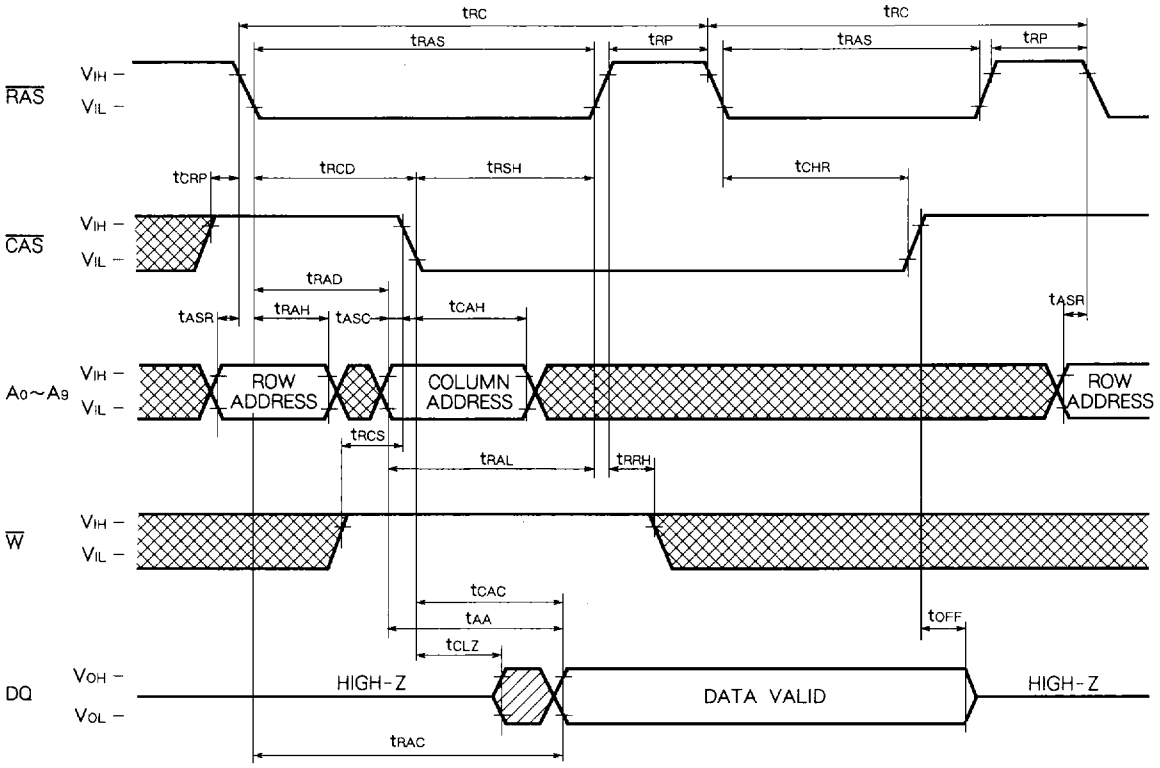
$\overline{RAS}$ only Refresh Cycle



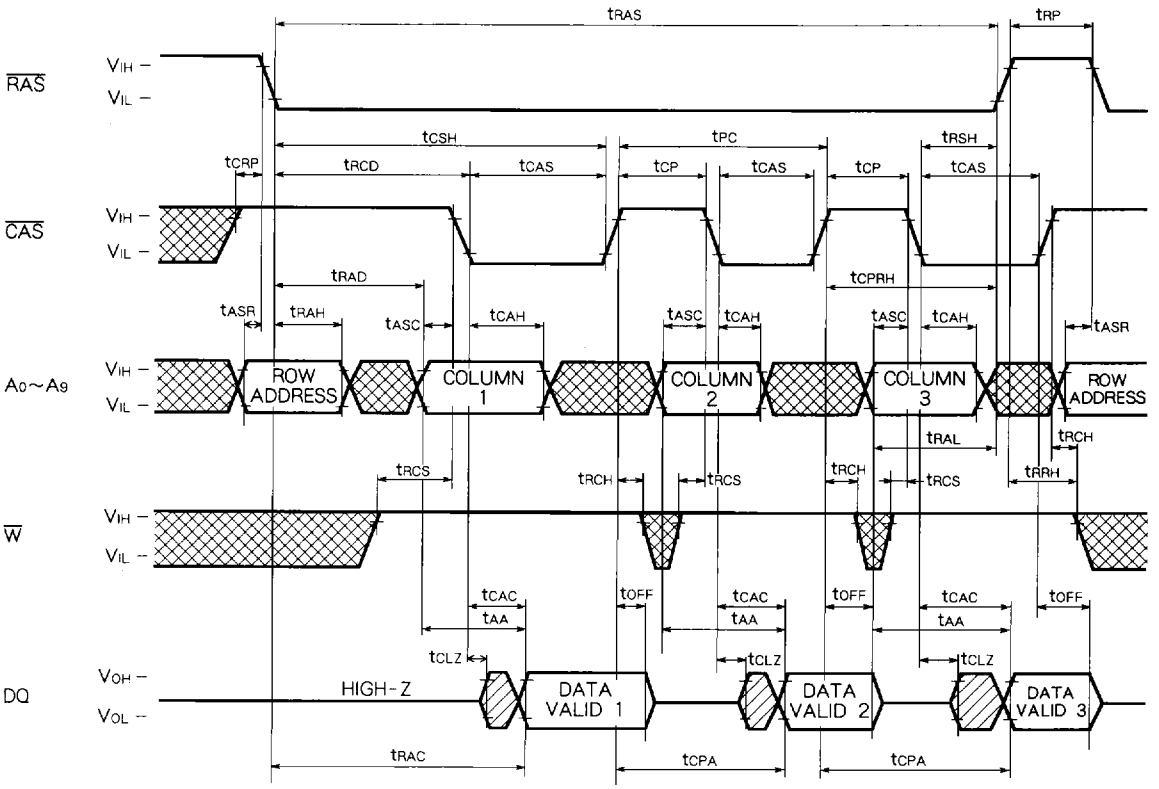
$\overline{CAS}$ before $\overline{RAS}$ Refresh Cycle



Hidden Refresh Cycle(Read)



Fast-Page-Mode Read Cycle



Fast-Page-Mode Early Write Cycle